CLAIM AMENDMENTS

1. (Currently Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a film to be processed on a substrate;

forming a mask material on the film to be processed;

forming a resist pattern on the mask material;

patterning the mask material using the resist pattern as a mask;

shrinking a patterned the mask material after patterning;

patterning the film to be processed using a shrunk the mask material, after shrinking, as a mask; and

removing the shrunk mask material.

- 2. (Currently Amended) The method for manufacturing a semiconductor device according to claim 1, wherein the mask material is a metal film is formed as the mask material.
- 3. (Currently Amended) The method for manufacturing a semiconductor device according to claim 2, wherein including

forming a ruthenium film is formed as the mask material, and

the shrunk mask material is removed removing together with the mask material and the resist pattern using in an oxygen-containing plasma.

4. (Currently Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a film to be processed on a substrate;

forming a ruthenium film as a mask material on the film to be processed;

forming a resist pattern on the mask material;

patterning the mask material using the resist pattern as a mask;

patterning the film to be processed using a patterned the mask material, after patterning, as a mask; and

removing the patterned mask material.

5. (Currently Amended) The method for manufacturing a semiconductor device according to claim 4, wherein including removing the patterned mask material is removed together with the resist pattern using in an oxygen-containing plasma.

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6. (Currently Amended) The method for manufacturing a semiconductor device according to claim 5, wherein including removing the patterned mask material is removed in the state that with a metal material is exposed on the substrate.